STATISTICAL APPROACH TO FLOW STRESS AND GENERALIZED HALL–PETCH LAW FOR POLYCRYSTALLINE MATERIALS UNDER PLASTIC DEFORMATIONS

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Abstract

A theory of flow stress is proposed, including the yield strength $\sigma_y$ of polycrystalline materials in the case of quasi-static plastic deformations depending on the average size $d$ of a crystallite (grain) in the range of $10^{-3}$–$10^{-1}$ m. The dependence is based on a statistical model of energy spectrum distribution in each crystallite of a single-modal polycrystalline material over quasi-stationary levels under plastic loading with the highest level equal to the maximum dislocation energy in the framework of a disclination-dislocation deformation mechanism. The distribution of an equilibrium scalar dislocation density in each crystallite leads to a flow stress from the Taylor’s strain hardening mechanism containing the usual (normal) and anomalous Hall–Petch relations for coarse and nanocrystalline grains, respectively, and gains the maximum at flow stress values for an extreme grain size $d_0$ of the order of $10^{-8}$–$10^{-7}$ m. The maximum undergoes a shift to the region of larger grains for decreasing temperatures and increasing plastic deformations. The maximum undergoes a shift to the region of larger grains for decreasing temperatures and increasing strains $\varepsilon$.

Keywords: yield strength, quantization of the grain energy, coarse-grained and nanocrystalline materials; stress-strain dependence.

Introduction

One of the main areas of research in materials science is the search for a possibility of controlling the internal defect substructure of crystallites in order to obtain the best strength and plastic properties of polycrystalline materials. An optimization of the above properties is impossible without the use of new technologies, the best known of which are the methods of severe plastic deformation (SPD), their combinations with recrystallization annealing, the vapor deposition method, etc [1]. These technologies allow for ample variations in orientation, linear sizes, $d$, of the elements of material microstructure: from meso-poly-crystalline and coarse-grained (CG, 10–1000 μm) to fine-grained (FG, 2–10 μm), ultrafine-grained (UFG, 0.5–2 μm), submicrocrystalline (SMC, 100–500 nm), and down to nanocrystalline (NC, <100 nm) samples. Experimental study of the physico-mechanical properties of polycrystalline materials (micro-hardness, $H$, yield strength, $\sigma_y$, ultimate stress, $\sigma_u$, and strain hardening coefficient, $\theta$) has revealed the features of the hardening mechanism in the transition to UFG, SMC and NC states for a given material. Systematic research for the influence of the structure parameters of a material on the strength properties under quasi-static deformation was initiated in [2,3] by the empirical Hall–Petch (HP) relation

$$\sigma_y(d) = \sigma_0 + kd^{1/2}$$

($\sigma_0$ and $k$ are the respective frictional stress for dislocations as they move inside the grains and the Hall–Petch coefficient), observed at the initial stage of the yield surface (Fig. 1c) in the diagram “$\sigma$=$\sigma(\varepsilon)$” (Fig. 1a), for materials either with grains of different sizes (such as Cu in Fig. 1b), or at the formal value $\sigma_y(d) = \sigma(d)_{k=0.0012} = \sigma_{0.2}(d)$ without a pronounced yield surface. This research was continued in the works of R. Armstrong, H. Conrad, U.F. Kocks, G. Langford, A.W. Thompson, J.G. Sevillano, S.A. Firstov, B.A. Movchan, V.I. Trefilov, Yu.Ya. Podrezov, V.V. Rybin, V.A. Likhachev, R.Z. Valiev, V.E. Panin, E.V. Kozlov, and N.A. Koneva, described in [4, 5]. For UFG, SMC and NC samples, the relation (1) shows a significant deviation, which requires a modification [6] of its right-hand side by a term quadratic in $d^{-1/2}$,

$$\sigma_y(d) - \sigma_0 = k_0d^{-1/2} + k_2d^{-1}$$

taking into account the parabolicity of the plot $(d^{-1/2}, \sigma_y(d))$, as well as the maximum at the yield strength associated with the so-called “negative value” of the Hall–Petch coefficient $k$, $k = (d\sigma_y)/(d(d^{-1/2}))$, in the region of the “anomalous” Hall–Petch relation. There are quite a few models whose purpose is to justify the feasibility of either the standard “linear” or the “quadratic” Hall–Petch relation, based on empirical

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approaches. Among them, for example, in [5] the following models are distinguished: the Kocks–Hirth, Arkharov–Westbrook, Mughrabi, Ashby, Koneva, Valiev, Kim–Estrin–Bush models, the dislocation hardening model, the “casing” model, and the three-dimensional composite models. Their peculiarity is the boundary hardening of grains by dislocation ensembles, including the so-called triple and quadrupole joints of grains, in connection with their contribution to (1), (2), and with the concept [8, 9, 10, 11, 12] of increased curvature-torsion of a crystal lattice (CL).

In the study of polycrystalline aggregates with two-phase materials, the problem of analyzing the behavior of flow stress (FS) as a function of the size of the grain (which is the main solid phase) and as the effect of grain boundaries in the soft (second) phase becomes more involved (the contribution of the soft phase increases to tens of percent in the transition to SMC and NC materials [13]) and was examined for metal, metal-ceramic and ceramic materials in the review [4]. Since the production of a uniformly sized grains of materials is technologically difficult, this leads to making allowance for distributions with respect to the grain size in a sample, and therefore also takes into account the specifics of calculations for plastic and strength parameters, in particular, FS and \( \sigma_y \). For such samples, beyond the relation (2) for FS and \( \sigma_y \) in the case of lognormal grain size distribution, a different model of dependence on the grain size was proposed [14, 15] for samples coated with Cr by magnetron sputtering [16]. The model takes into account a deviation from the strictly quadratic dependence (2) for \( d < d_{c1} \) by using the S-integrals technique combining three relations: (1) for \( d_{c1} < d \) \( (d_{c1} = (k_f/k_0)^2 \leq 0.5 \mu\text{m}) \), (2) for \( d_{c2} \leq d \leq d_{c1} \) \( (d_{c2} \leq 0.1 \mu\text{m}) \), and the new relation (for \( d < d_{c2} \))

\[
\sigma_3 = \left[ 1 - \left( \frac{d}{d_{c1}} \right)^2 \right] \sigma_{gb} + \left( \frac{d}{d_{c2}} \right)^2 \sigma_{rh},
\]

where \( t \), \( \sigma_{gb} \), \( \sigma_{rh} \) are the respective thickness, ultimate strength of the grain boundary, and theoretical ultimate strength for the grain. At the same time, as we assume a biquadratic dependence on \( d^{-1/2} \) with large values of \( (\sigma_{gb}; \sigma_{rh}) = (2;12) \text{ GPa} \), the model allows us to go over to the NC region, where the
anomalous (inverse) Hall–Petch law holds true [17–21], with a decrease in FS and $\sigma_y$, as $d^{-\alpha_2}$ increases at $d < 100$ nm.

Among the theoretical models that lead to a simultaneous description of the normal and anomalous Hall–Petch laws for $\sigma_y$ and microhardness $H$, one can distinguish, first of all, “the mixed model of the plasticity of polycrystalline metals, supplementing dislocation plasticity inside the grains by the mechanism of slipping along the grain boundaries”, on the basis of the Maxwell strong viscous liquid in the framework of molecular dynamics simulation for Cu and Al [22]. Secondly, the dislocation kinetic model of G.A. Malygin [23, 24] on the basis of a first-order evolution equation for the average dislocation density $\rho'=\rho(t)$ in the grain,

$$\frac{d\rho}{d\gamma} = \frac{\beta}{bd} - (k_a+k_b)\rho, \quad k_b = 4\eta_b \frac{D_{gb}}{\gamma d^2}, \quad \eta_b \approx \frac{Gb^3}{k_BT}, \quad (4)$$

within the framework of the Taylor’s strain hardening mechanism [25]. In obtaining (4), it was assumed [23, 24] that the time dependence $\rho=\rho(\gamma(t))$ is implicit through the uniaxial tensile strain (or compression) $\varepsilon=\gamma/m$, $d\rho/dt=\dot{\gamma}d\rho/d\gamma$, with a constant strain rate $\dot{\gamma}=\dot{\gamma}/m$ and shear strain rate $\dot{\gamma}=b\rho u$, for the Burgers vector module $b$, dislocation velocity $u$, Taylor orientation factor $m=3.05$, and also for $(\beta,k_a,k_b; D_{gb}, G, k_b, T)$, being, respectively, the coefficients determining the intensity of dislocations accumulated in a grain volume and the annihilation of screw and edge dislocations, the grain-boundary diffusion coefficient, the shear modulus, the Boltzmann constant, and the absolute temperature. The model realizes a competitive process of proliferation and annihilation of dislocations, which depends on a sufficiently large number of external parameters. Finally, one also considers some models with 3D dynamics of discrete dislocations [26, 27, 28].

The general conclusions from the theoretical and experimental works known to date with respect to FS and $\sigma_y$ are the following observations:

1) the maximum of $\sigma_y$ is achieved for some materials at certain values of the crystallite (grain) diameter $d_0$ in the NC region at a given $T$ and plastic deformation (PD) rate $\dot{\gamma}$;

2) $d_0$ is shifted to the region of coarse grains with increasing $T$ and independently with decreasing $\dot{\gamma}$;

3) in the regions of coarse and NC grains there is no physical model describing the normal and anomalous HP laws at the same time, based on a statistical approach to the spectrum of crystallite energies considered as the main (solid) phase of polycrystalline materials with a fixed PD, depending on the distribution of a dislocation ensemble.

The ongoing discussion concerning the ways of forming of 1D defects (dislocations) as emerging from 0D defects (in particular, nanopores, vacancies and other zones of localized deformation) due to the lack of unambiguous interpretation of experimental data makes it possible to assert that there is no strictly well-founded fundamental theory taking into account the defect substructure of a crystal lattice (CL) that would lead to a Hall–Petch-type relation in all grain ranges for a polycrystalline material under PD. The twin types defects (2D defects), which is prevailing in NC materials are always generated by means of the dislocation being permitting to present the former as the dislocation combinations. It should be noted that the cases of the normal (CG materials) and anomalous (SMC and NC materials) Hall–Petch relations actually correspond to the radiation of an absolutely black body, exhibiting the Rayleigh–Jeans (long-wave) and Wien (short-wave) regions in the plot $(\omega,u(\omega,T))$ for the spectral density of radiation energy $u(\omega,T)$ (with the dimensionality $[u(\omega,T)]=\llbracket\sigma_y\rrbracket\cdot1s=1eV\cdot1s^{-1}\cdot m^{-3}$), united in the framework of Planck’s theory [29], based on the discreteness of radiation energy spectrum for atoms in an absolutely black body.

The purpose of this article is to construct a theoretical model for the emergence and evolution of a defect structure, including 0D (nanopores, bi-nanopores, ...) and 1D (dislocations) defects in the grains of a being loaded polycrystalline aggregate, based on a statistical approach to the energy spectrum of each grain, in view of the integral nature of FS and $\sigma_y$. The latter point is a crucial one due to the complexity of a direct solution of the Schrödinger equation (in partial derivatives of order no less than $3\cdot10^{12}$) for a crystallite in an external mechanical deformation field of $N=10^{12}$ atoms (corresponding to $d=a\cdot N^{1/3} = 3 \mu m$, for the lattice constant $a=0.3$ nm), even with the help of advanced supercomputers.
The article involves the consideration (in the next section) of a scenario for the emergence from a sequence of 0D defects (nanopores, localized deformation zones) of an edge dislocation, complete with an estimation of its energy. Then, a model is introduced for the distribution of crystallite energies in a polycrystalline single-mode material with respect to quasi-discrete levels in a state of thermodynamic quasi-equilibrium at a fixed value, \( \varepsilon \), of PD. The following section is devoted to deriving the relation for equilibrium (e.g. corresponding to annealed polycrystalline materials) scalar dislocation density and FS, and also to a generalized HP law for \( \sigma_y \). The article is completed by planning to compare with the experimental data for \( \sigma_y \), involving a number of materials, and is followed by some conclusions.

A grain is understood as a crystallite with an initial (prior to PD) density of dislocations.

**Emergence scenario for deformation-induced dislocations and properties of dislocation energy**

In order to formulate the model, we introduce a definition that allows a uniform description of 0D (zero-dimensional) and 1D (one-dimensional) CL defects, using a representation reminiscent of the Frenkel–Kontorova model, proposed in the 1930s, with 0D defects “rarefaction dislocation” type (“holes” in a CL). We consider as the models the non-metallic and metallic solids with a cubic CL. For the former model one of six (e.g. covalent) bonds among the atoms connecting an atom in a CL node with the other atoms wherein, as a result of an elementary PD act by tensile strain, undergoes a rupture (breaking the common electron pair in the outer electron shell of two atoms) significantly displacing the two atoms participating in the deformation with the emergence of a 0D defect – nanopore. Nanopore represents the localized deformation (or plasticity) zone, for given case being by 0D-dimensional one. Its appearance seems to be natural within thermo-fluctuation mechanism, under which the collective oscillations of atoms (beyond the elasticity limit of the sample) are such that in one of the antinodes, when they interfere, it is accumulated an energy being larger than the bonding energy between the atoms (in order to create a stress locally to be more than Peierls-Nabarro stress \( \tau_{PN} \) in a crystallographic plane containing these atoms). A concrete place of appearance of nanopore is random. The most probable event is an appearance of a nanopore at the surface of the sample (or from the grain boundary). Such antinode may be born in the region, where two or more atoms are localized, thus leading to disconnecting of 2 and more bonds and therefore to appearance of the large nanopore: n- nanopore, n=2,… For a single-layer material the dislocations can be only in the layer’s plane (e.g., for graphene with a hexagonal CL, they can be generated by pair of the Stone-Wales defects when breaking zigzag symmetry [30]), whereas for dislocations (to be perpendicular to the layer) this is the degenerate case of a pair of dislocations, each containing an atom on its axis (0D defect) and having no specific Burgers vector (see Fig. 2a for a cubic CL). For a two-layer material (e.g., AB- or AA-stacked bilayer graphene), the mechanical power supplied under PD to a unit cell and sufficient to break the bonds in a layer between two atoms, as well as the bonds in the other layer between two atoms combined by orthogonal projection (Fig. 2a), leads to an emergence of two unit edge dislocations with parallel axes of the length \( L=a \), which is the lattice constant, being the modulus \( b \) (\( b=a \)) of the Burgers vector for each of the dislocations.

An example scenario of statistical emergence for a pair of edge dislocations under a sequence of single plastic deformation acts with intermediate nanopores in a crystallite sample with a cubic CL is given in Fig. 2.
Fig. 2: The formation process for a pair of rectilinear edge dislocations starting from a growing nanopore (being developed) upon stretching along AA’ in the crystallographic slip plane. In Fig. 2a, for a nanopore formed at the discontinuity between the nodes A and A’ it is shown that in the nodes B, C (B’,C’) neighboring with A(A’) there is a formal resultant Newton force R (additional to the external force and indicated in red, in turn equivalent to tensile stress), leading to a formation process for the bi-nanopore in Fig. 2b. For the same reasons, the 3- nanopore in Fig. 2c, with the exit of the boundary points F and F’ of the n-nanopore to the surface from the left in Fig. 2d and then to the surface to the right of the boundary points Z and Z’, there are already m- nanopore (m>n) in Fig. 2e, with the formation of a pair of edge dislocations of the length L=mb having opposite Burgers vectors. Further in Fig. 2f (in the direction perpendicular to Figs. 2a–2e), the atomic half-planes that are bounded from inside by dislocation axes move apart under tension, i.e. the dislocations move on with their steps exiting to the crystallite surface, while the adjacent atomic planes parallel to these half-planes are drawn into the empty space due to inter-atomic forces, thus forming the defect packaging (subtraction). In dependence from the magnitude of the thermal fluctuations the k-nanopore, k>1 can be initially generated in any place of the grain, but more probably from its surface as in case of CG sample (see Eq. (15) and comments below).

For metallic PC samples, dislocations can be born in the atomic planes preferably in a direction with least energy of defect packaging (subtraction or inserting) according to the scenario similar to one presented on the Fig. 2 with own specific in BCC, FCC, HCP CLs with preliminary forming of nanopores, as the zone of localized plasticity (known as well as the band of localized deformation\(^8\)). In case of developed dislocation structure, the new dislocations inside the grains can be finalized on already present dislocations in the grain, whereas in the flow region for PC materials the pole Frank–Read mechanism [32] of generating the dislocations, especially for CG—UFG materials is valid, which, in turn having the zone of localized plasticity as the necessary condition to proliferate the driven dislocations from given one.

The emergence time for the nanopore in Fig. 2a at the PD rate \(\dot{\varepsilon}\) is estimated as \(t_0 = \frac{b}{(\dot{\varepsilon}d)}\), where \(l\) is the length of the crystallographic plane along AA’, and \(b = a\) is the interatomic distance. For \((\dot{\varepsilon}; b; l) = (10^{-3}\text{s}^{-1}; 0.3\text{nm}; 10^{-3}\text{m})\), the estimate \(t_0 = 3\cdot10^{-4}\text{s}\) holds true. Further, after a short time, \(\Delta t << t_0\), of relaxation to a new equilibrium position, the formation of a bi-nanopore (Fig. 2b) is more advantageous than the formation of nanopore in another place on this plane, since the atoms adjacent to \(A(A’) B, C (B’,C’)\) experience resultant forces additional to the external forces (equivalently, gradient of tensile stresses). Thus, the process of n- nanopore formation from the initial nanopore proceeds rapidly up to its boundary points on the \(F, F’\) plane (Fig. 2d) and is then followed (Fig. 2e) by the formation of a pair of edge dislocations on the axes \(FZ, F’Z’\), whose Burgers vectors are opposite and perpendicular to the plane of the figure. Then, the dislocations diverge (Fig. 2f), followed by a characteristic collapse of the neighboring planes parallel to the plane of Figs. 2a–2e, due to the permanently tunable spectrum of energy levels (when dislocations move) for the atoms in these and neighboring atomic planes, admitting some new stable (e.g. according to the Landau–Zener mechanism) interatomic bonds with a new electronic structure. As a result, when the forces that bind the atoms on the dislocation axes with the atoms on the neighboring planes become stronger than the stretching PD forces, the usual picture is reproduced for a unit dislocation [33] with a far-gone stationary second dislocation. After the forming of \(m\)- nanopore, the shear, perpendicular to the direction of PD, can be by a competing way instead of tension, with the re-

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\(^2\) In the zone of localized plasticity under the high-level local internal stresses one can take place so called martensitic transformations, which provides as for the austenitic steels direct transition from FCC \(\gamma\)-phase of CL in BCC \(\alpha(\alpha’)\)–phase, and then, inverse transition with forming the 2D twin type defects or dislocations by means of combinations of partial Shockley dislocations with account of the change of the shear direction at direct and inverse transitions, empirically justified in [31]
spective change of the grain orientation, at which the dislocation axes: \( FZ, F'Z' \), are shifted relatively the tension direction in different sides in the Fig. 2e

Some remarks are in order. First of all, the instantaneous emergence of a large dislocation under PD without any intermediate 0D-defects in multilayer crystallites is in contradiction with the finiteness of the interaction velocity. Secondly, we select two time scaling: the fast one \( t_d \approx N \Delta t \) for forming of a dislocation, from a sequence of nanopores and the slow one proportional to \( t_0 = b/(\dot{\varepsilon}d) \) \((t_d \ll t_0)\) for enumerating the PD acts. Thirdly, an experimental confirmation of dislocation emergence on the basis of a given sequence of nanopores requires precise measurements in view of the transience of dislocation process, and also due to the blurring (justifying the emergence of nanopores) of a diffraction pattern due to the screening of the plane containing the nanopores by the neighboring parallel atomic planes. Fourth, the above scenario for the emergence of a screw dislocation followed by a mixed dislocation may also be investigated (we leave this problem outside the scope of the paper).

The above analysis makes it natural to extend the notion of dislocations (originally introduced by V. Volterra in 1905, followed by E. Orowan, M. Polanyi and G. Taylor in 1934 for the edge dislocation, and afterwards by J. Burgers [33] in 1938 for the screw dislocation) by a definition according to F.Ch. Franck given, for instance, in [33, 34, 35], where a following (second) dislocation in the same crystallographic slip plane with the opposite Burgers vector is far removed by the action of loading (stretching).

We refer to a **generalized dislocation** (GD) with its axis (of length \( na \)) consisting of \((n+1)\) atoms \((n \text{ segments})\) as a topological defect of physical spatial dimension, \(D, D \leq 1\), for which there exists at least one closed Burgers contour around its axis at the distance of no less than the \( a\)-atomic lattice constant, which determines the Burgers vector \( b\), being constant along the axis (line) of a generalized dislocation, with the possible exception of the end points.

The rule for determining the direction and magnitude of the Burgers vector remains the standard, according to the rule of the “right screw” [33]. When the GD ends exit to the boundary of a crystallite, or in the case of their coincidence (the formation of a loop), we have an usual dislocation, being of edge, screw or mixed types. Otherwise, the GD represents an incomplete dislocation of one of these types if there are more than one crystal lattice nodes on its axis with the Burgers vector on the dislocation axis that is undetermined only at its finite points, or else, if the dislocation, with its ends being identical, represents a 0D defect, being a nanopore in a limiting case of dislocation. An incomplete dislocation on whose axis there are \( n \) atoms \((n>2)\) always has a closely-seconded second incomplete dislocation, thus resulting in an \( n\text{-nanopore} \) (see Figs. 2a–2d for a nanopore, bi-nanopore, 3-nanopore and \( n\text{-nanopore} \)). A rectilinear \( n\text{-nanopore} \) implies the presence of \( n \) “holes” of empty CL nodes in the interval. Such a sequence of 0D defects actually has two axes of \( n \) atoms each \((ED, E'D' \text{ in Fig. 2c; } FG, F'G' \text{ in Fig. 2d})\), being parallel and spaced by the distance \( 2a \), except the ends \((E \text{ and } E', D \text{ and } D', G \text{ and } G')\), spaced by the distance \( a \). It is such axes of incomplete dislocations that we understand as the axes of two GDs characterizing an \( n\text{-nanopore} \) from the zone of localized deformation.

Dislocations create elastic stress fields with a tensor, \( \sigma_{ik}, i,k = 1,2,3 \), that define the field of elastic strains with a tensor, \( u_{ik}, \) in the crystallite with a shear modulus \( G \), so that the analytically free energies of screw, edge and mixed dislocations of length \( L \), with the Burgers vector \( b \) in the crystallite are calculated by the rule [34] (with free energy \( F \)): 

\[
F = \frac{1}{2} \sum_{k=1}^{3} u_{ik} \sigma_{ik} dV,
\]

respectively

\[
E_d^{\text{screw}} = \frac{Gb^2L}{4\pi} \ln \left( \frac{R}{r_0} + Z \right), \quad E_d^{\text{edge}} = \frac{Gb^2L}{4\pi(1-\mu)} \ln \left( \frac{R}{r_0} + Z \right), \quad E_d^{\text{mix}} = \frac{Gb^2L}{4\pi K} \ln \left( \frac{R}{r_0} + Z \right).
\]

(5)

Here, \( \mu, R, r_0, Z \) are, respectively, the Poisson ratio of a material \((0.1 < \mu < 0.4)\), the radii of dislocation zone \((\text{the cut-off parameter } R, \text{ usually, } R = n \cdot 10^6 b)\), of the dislocation core \((\text{axis} ) r_0 \approx 3b\), the correction constant \(1 < Z < 3\) for estimating the energy near the dislocation core and \((1-\mu) \leq K \leq 1\).

The energies of edge and screw dislocations are nearly the same and have the following properties:

1. the energy of a dislocation is proportional to its length: \( E_d^{\text{mix}} \sim L \);
2. the energy of a unit dislocation of length \( L_e = b \) at \( R \sim L_e \) equals to \( E_d^{L_e} = \frac{1}{4} G b^2 L_e = \frac{1}{4} G b^3 \); for a polycrystalline material with \((G, b) = (30 \text{ GPa}, 3 \cdot 10^{-10} \text{ m})\) it equals to: \( E_d^{L_e}(G, b) = 2.53 \text{ eV} \);
3. the dislocation energy containing \((n+1)\) atoms on (for full dislocation) a dislocation axis\(^3\) equals to the sum of the energies of \(n\) unit dislocations \(E_d^n = nE_d^L\);
4. a dislocation with a smaller module of the Burgers vector \(b_i\) of the same length \(L\), as a dislocation with \(b=mb_i\), is energetically more advantageous at its formation, since \(E_d^L(G,b) = m^2E_d^L(G,b_i)\);
5. the energy of a unit dislocation exceeds by two orders the energy of thermal fluctuations of an atom, \(k_BT\), at \(T=300\) K: \(E_d^L(G,b)/k_BT = (2.53\text{ eV})/(0.026\text{ eV})\);
6. the energy \(E_d^L\) with the smallest Burgers vector is comparable with the activation energy of an atom \(E^\text{act}\) in the course of diffusion. Indeed, in the diffusion coefficient, we have \(D = D_0e^{-(E^\text{act}/k_BT)}\), with the frequency factor \(D_0\) for the most metals being \(E^\text{act}\in[1 \text{ eV}, 4\text{ eV}]\) [36]. So for copper, \(\alpha\)-iron, niobium, \([E_d^L, E^\text{act}](Cu)=[2.31;2.05] \text{ eV}; [E_d^L, E^\text{act}](Fe)=[3.93;3.05]\text{eV}; [E_d^L, E^\text{act}](Nb)=[4.21;4.13] \text{ eV}\) at \(T=300\text{K}\) and \((G,b)=(37.5 \text{ GPa}; 3.30\cdot10^{-10}\text{m}), for Nb with BCC lattice at \(b\) equal to its CL constant (for Cu and \(\alpha\)-Fe, see Table 2 [37]);
7. for a crystallite being a polyhedron of diameter \(d\) inscribed in a sphere, the largest rectilinear dislocation lies in one of the equatorial slip planes passing through the center of the crystallite, and the largest loop dislocation coincides with the equator of the polyhedron slip plane (Fig. 3), having the respective length and energy

\[
(L;L_d) = (1;\pi)d = (N;\pi N)b,
\]

\[
E_d^N = \frac{Gb^3d}{4\pi K} \ln \left(\frac{R}{r_0} + Z\right)(1;\pi) = \frac{Gb^3N}{4\pi K} \ln \left(\frac{R}{r_0} + Z\right)(1;\pi), \tag{6}
\]

where \(N = [d/b;\pi d/b]\) is the number of atoms on the corresponding dislocation axes, and the square brackets denote the integer part of the fractions \(d/b\) and \(\pi d/b\). In the first place, it follows that an \(n\)-nanopore and two parallel dislocations of \(n\) atoms on their axes are comparable energetically. Secondly, it is advantageous to realize dislocation ensembles under PD by corresponding crystallographic slip systems with the smallest Burgers vector \(b\), including partial dislocations, especially for materials with FCC or BCC lattices. On the basis of property 6, one can make an approximate assumption that the energy of an arbitrary dislocation may be estimated analytically by using the activation energy (determined experimentally) of the atoms that form the axis.

**Statistical model of crystallite energy distribution for quasi-static PDs**

Consider a polycrystalline single-modal metal aggregate of volume \(V\) with an arbitrary CL, being homogeneous with respect to the size of crystallites closely packed in the form of polyhedra (of diameter \(d\)) distributed isotropically throughout the sample. We consider the PC aggregate in a fixed phase state being constant within a considerable range of temperatures \([T_1,T_2]\) (Fig. 3). We restrict ourselves to the case of a cubic CL with the smallest Burgers vector of an arbitrary dislocation coinciding with \(a, b=a\).

![Fig. 3: A multilevel model of a polycrystalline sample with uniformly sized (single-modal) crystallites and a crystallographic slip plane passing through the crystallite center.](image)

Let the process of quasi-static mechanical loading (stretching) of a sample with a constant strain rate, \(\dot{\varepsilon}:\dot{\varepsilon}\in[10^{-5}, 10^{-3}]\text{ s}^{-1}\), begin at the time instant \(t_0=0\) and the temperature value \(T\). When the elastic

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\(^3\)The axes of partial dislocations not necessary contain the atoms on its axis, but consist from the elementary segments, which lengths are proportional their Burgers vectors. Further, if otherwise stated we discuss only full dislocations.
limit \( \sigma_c \) is reached, with the conditional value of limiting elastic deformation \( \varepsilon_{0.05} = 0.25 \cdot \varepsilon_{0.2} \), a PD starts to emerge in crystallite nanopores and dislocations, accompanied by energy exchange between the atoms released from the CL nodes and the nanopores caused by the CL breaking. When the residual PD \( \varepsilon_{0.02} \), albeit \( \varepsilon > \varepsilon_{0.05} \) (corresponding to \( \sigma_Y \) for \( \varepsilon = \varepsilon_{0.2} \)) is reached at the instant \( t = \varepsilon / \dot{\varepsilon} \), \( t > t_1 = \varepsilon_{0.05} / \dot{\varepsilon} \), with a fixed external loading \( (\varepsilon = 0) \), or decreasing slightly to avoid rapid creep \( (\varepsilon \text{ increasing at } d\sigma/d\varepsilon = 0) \) the state of thermodynamic quasi-equilibrium (see Footnote 4) is established for each crystallite within a certain time interval.

The following points are crucial for the model (some of them, namely, items 1, 2, 4, describe mathematically a probability space \((\Omega, \mathcal{U}, P)\) of events for the crystallites of PC sample under PD:

1. The spectrum of mechanical energy for each crystallite at a PD value \( \varepsilon \) consists of discrete levels, \( E_d^0, E_d^1, E_d^2, \ldots, E_d^n, \ldots \), depending on \( \varepsilon \) and starting with the lowest energy level \( E_d^0 \) of an ideal crystal, followed by the levels \( E_d^1 \) for a crystallite with a unit dislocation, and then by the levels \( E_d^2 \), with a dislocation of (axis) length \( 2b \), \( E_d^n \), the dislocation of length \( L = nb \), \( \ldots \), and also with \( E_d^N \), being the energy of the maximum rectilinear dislocation \((6)\). With each elementary PD act, the crystallite either acquires or loses (local restoration of crystallinity) a 1D defect with \( n \) atoms on its axis with the energy values \( E_d^n \), for \( n = 0, 1, \ldots, N, \ldots \). For each PD act, it is possible to expect the appearance of (curvilinear) dislocations with a large number \( N \) of atoms on the axis \( N_d/2 > N > N_d \), with \( N_d \), being the number of crystallite atoms;

2. At an arbitrary time instant \( t \) each crystallite may be in a state with \( m_1 \) unit dislocations, with \( m_2 \) dislocations having 3 atoms on the axis; \( \ldots \), with \( m_n \) dislocations having \((n + 1)\) atoms on the axis \( \ldots \), with \( m_N \) maximum rectilinear dislocations for \((0, \ldots, 0) \leq (m_1, m_2, \ldots, m_n, \ldots, m_N) \), with the mechanical energy \( \sum_{m=1}^{N} m_n E_d^n \) induced by dislocations with no allowance made for the energy of elastic deformation;

3. The minimal time \( \Delta t_0 \) between elementary PD acts, under which the crystallite is enlarged by the value \( d(1 + \varepsilon) \Delta E = b_\varepsilon \) is connected with the appearance of two dislocations of the opposite sign (with effective Burgers vectors \( b_\varepsilon \) and \(-b_\varepsilon\)) lying in the crystallographic slip plane passing through the center of a crystallite, for given value \( \varepsilon \) of residual deformation. Because of PD homogeneity, we assume \( b_\varepsilon = b(1 + \varepsilon) \). By the time instant \( t = (\varepsilon - \varepsilon_{0.05}) / \dot{\varepsilon} \), the interval \( \Delta t_0 \) is determined from the condition (for stretching along the \( z \) axis with \( \varepsilon = u_{31} \)):

\[
\varepsilon - \varepsilon_{0.05} + \Delta \varepsilon = \dot{\varepsilon} t + \dot{\varepsilon} \Delta t_0 \quad \Rightarrow \quad \Delta t_0 = \frac{\Delta E}{\dot{\varepsilon}} = \frac{b_\varepsilon}{\dot{\varepsilon} d (1 + \varepsilon)} = \frac{b}{\dot{\varepsilon} d}.
\]

One such tube along the \( z \) axis with the cross-sectional area \( (b_\varepsilon)^2 \) in a given plane is sufficient to deform the crystallite by the measurable value \( \Delta \varepsilon \); however, because of the “explosive” nature of dislocation formation, such are virtually all the tubes in the slip plane, where the GD (nanopore and then dislocation) is generated. In view of polyhedral nature of the crystallite, there may be several closely situated tubes (then different atomic planes with GD) in the neighboring slip planes being parallel to the one under consideration. Deformations with the value \( \Delta \varepsilon \) occur in almost all of the crystallographic planes of the crystallite spaced by the distance \( nb, n = 1, \ldots, \left[ \frac{\dot{\varepsilon} d}{4n b^2} \right] \), albeit with different time intervals \( \Delta t_n = b/\dot{\varepsilon} (\sqrt{d^2 - 4n^2 b^2}) > \Delta t_0 \). The minimal number of dislocations \( N_0 \) that arise during the time \( t \) in order to achieve the residual PD value \( \varepsilon \) is determined by the relation (taking into account their emergence in pairs):

\[
N_0 = 2m_0 t/\Delta t_0 = 2m_0 \varepsilon d/b.
\]
In (8), \( m_0 \) is a polyhedral parameter to be taken into account how many crystallographic planes contribute to the crystallite deformation due to its polyhedral character (Fig. 4). Note, that it is not every elementary PD act that is accompanied by an emission of dislocations. Sometimes it is even a pair of dislocations formed in the previous PD act and diverging in the slippage plane by the value \( b_z \), thus realizing the case of mobile dislocations, that is sufficient to restore the CL translational symmetry in the vicinity of these GDs, due to the mutual attraction of the nearest parallel planes (Fig. 2).

The isotropy of distribution of crystallites implies for a cubic CL that the distribution of crystallographic slip planes relative to the loading axis \( z \) inside the angle \([- \frac{\pi}{4}, \frac{\pi}{4}]\) is such that the minimal average value of the number of dislocations in an arbitrary grain is equal to \( N_0 / \sqrt{2} \). The case of anisotropic distributions of crystallites (textures) makes it necessary to introduce a texture factor \( K = K(\alpha, \beta, \gamma) \) when calculating the average number \( \bar{N}_0 = \langle KN_0 \rangle \) over all the crystallite configurations in a PC sample.

4. Let us determine the probability for any of the possible defects in an elementary PD act to occur at the time instant \( t = (\varepsilon - \varepsilon_0) \bar{\tau} \), considering the state of thermodynamic quasi-equilibrium\(^4\) of a crystallite (with a fixed external loading) corresponding to an equidistant crystallite spectrum with a step equal to the energy of a unit dislocation for the residual plastic deformation \( \varepsilon = \dot{\varepsilon} t + \varepsilon_{0.05} \) in accordance with the Boltzmann distribution:

\[
\Delta E_{n+1,n}(\varepsilon) = E_{n+1}(\varepsilon) - E_n(\varepsilon) = \frac{1}{2} Gb^3, \quad \forall n = 0, 1, \ldots, N = \left[ \frac{d}{b} \right], \ldots.
\]

\[
P(E_n, \varepsilon) \equiv P_n(\varepsilon) = A(\varepsilon) e^{-\frac{\Delta G_0}{a} / k_B T}, \quad n = 0, \ldots, N, \quad A(\varepsilon) = \frac{e^x - 1}{e^x - 1},
\]

\[
A(\varepsilon) = \frac{e^x - 1}{k_B T d},
\]

where it is taken into account that \( E_n(\varepsilon)/E_n(\varepsilon) = E_n(0)/E_n(0) \) and \( E_n(0) \equiv E_n \).

In general, the process of PD of the crystallite and PC aggregate represents a non-equilibrium process in view of the change of \( \varepsilon \), because of \( P_1(\varepsilon_1) > P_2(\varepsilon_2) \) for \( \varepsilon_1 > \varepsilon_2 \). However, the quasi-statics of external loading allows one to present a PD process as a sequence of equilibrium processes changing (skipping from one to another) at a change of \( \varepsilon \) if the relaxation time \( \tau \) for the crystallite atoms after the PD act in a stable position (a new position in the CL) is much less than the minimal time between neighboring PD acts. A natural estimation for \( \tau \) is \( \tau = a/\nu = (0.3 \times 10^{-3})/0.1 \times 10^{-12} \) sec, as compared to \( \Delta t_0 = 2.47 \times 10^{-9} \) sec with the strain rate \( \dot{\varepsilon} = 10^{-3} \) c\(^{-1}\), ensures the correctness of the choice for probability distribution (10) according to Boltzmann for every crystallite with a fixed \( \varepsilon \). Under a high rate of loading, \( \dot{\varepsilon} = 10^{-3} \) c\(^{-1}\), the condition \( \Delta t_0 > \tau \) does not hold, so that the representation (10) is invalid. Thus, the probability distribution \( P(E_n, \varepsilon) \) for any possible defects of an elementary PD act in a crystallite has a smooth dependence on the strain \( \varepsilon \), \( P(E_n, \varepsilon) = f_n(\varepsilon)P(E_n, 0) \), so that the quantities \( f_n(\varepsilon) = [A(\varepsilon)/A(0)] (P(E_n, 0)/A(0))e^{(3+3\varepsilon+\varepsilon^2)} \) are the non-decreasing functions with \( P(E_n, \varepsilon_1) > P(E_n, \varepsilon_2) \) for \( \varepsilon_1 > \varepsilon_2 \). Note we have chosen the factors \( f_n(\varepsilon) \) in (10) as a natural multiplicative scaling of the probabilities \( P(E_n, 0) \). In general, dependence of \( P(E_n, \varepsilon) \) on \( \varepsilon \) may be arbitrary.
We assume items 1, 2, 4 to be valid for a quasi-static PD with \( t \geq t_1 \). The space \( \Omega = \{ E_{d}^{1}, E_{d}^{2}, \ldots, E_{d}^{n}, \ldots, E_{d}^{N}, \ldots \} \) of elementary events is defined for every crystallite in a state of thermodynamic quasi-equilibrium and is described by the occupation numbers \( \bar{N} = (m_1, m_2, \ldots, m_n, \ldots, m_N) \) of the corresponding defects, as well as in terms of the probabilities of elementary events (10), which depend on the residual PD via the effective energy \( E_{\bar{N}}^{\varepsilon} (\varepsilon) = \frac{1}{2} G b \bar{n}^2 \), and therefore also on the time instant \( t \). At small PD values, \( \Delta \varepsilon = \varepsilon, \) the factor \( M(\varepsilon) = \frac{1}{2} G b \bar{n}^2 / (k_B T) \approx \frac{1}{2} G b^3 / (k_B T) = M(0), \) that determines the energy scale of a dislocation emergence is the inverse of speed sensitivity [23,24]. The energy value of an elastic deformation with \( \varepsilon_{0.05} = u_{33} \) depends cubically on the crystallite size \( d \), and, for example, for \( \alpha\text{-Fe}, \) per atom, we have \( F_{a}(\varepsilon) = 2G \frac{(\mu^2 + 1)}{1 - 2\mu} \varepsilon_{0.05}, \) \( m_n = 0.25 \cdot 10^{-5} \text{eV} \sim 10^{-4} k_B T \) at \((\mu, m_n, \bar{p}) = (0.29, 9.3 \cdot 10^{-26} \text{kg}, 7800 \text{kg/m}^3)\). The minimal time intervals between PD acts necessary to form a unit dislocation (nanopore) for \( \alpha\text{-Fe} \) in a CG \((d_i=10^{-4} \text{m})\) and NC \((d_2=10^{-7} \text{m})\) samples at \( \dot{\varepsilon} = 10^{-5} \text{s}^{-1} \) according to (7) are equal to \((\Delta t_01, \Delta t_02) = (2.47, 2.47 \cdot 10^{-3}) \) \( 10^{-1} \text{s}^{-1} \). The latter corresponds to a small change of the defect structure of crystallites in NC materials as compared to CG ones with an equal PD. In addition, to the scale factor presented in the probability definition (10), there is an implicit influence of the grain boundary (soft phase) through the energy \( E_{\nu} (d) = E_{d}^{N} \) of maximal dislocation.

The transition of a crystallite from a state with energy \( E_{\bar{N}_1} = \sum_{n=1}^{N} m_n E_{d}^{n} \) to a state with energy \( E_{\bar{N}_2} = \sum_{n=1}^{N} m_n E_{d}^{n} \) (for \( \bar{N}_2 > \bar{N}_1 \) to be lexicographically ordered) is realized due to the absorption by the crystallite of the energy supplied by external mechanical loading with energy \( L \Delta \varepsilon \) at an elementary PD act when the PC sample is lengthened on \( \Delta \varepsilon = b / d; \)

\[
E_{\bar{N}_2} (\varepsilon + \Delta \varepsilon) = E_{\bar{N}_1} (\varepsilon) + M \Delta \varepsilon \quad : \Delta E_{\bar{N}_1 \bar{N}_2} (\varepsilon) = E_{\bar{N}_2} (\varepsilon) - E_{\bar{N}_1} (\varepsilon) = \sum_{n=1}^{N} (m_{2n} - m_{1n}) \frac{1}{2} G b^2 \varepsilon
\]

\[
\frac{E_{\bar{N}_2} (\varepsilon + \Delta \varepsilon) - E_{\bar{N}_1} (\varepsilon)}{\Delta \varepsilon} = L + o (\Delta \varepsilon),
\]

which describes the conservation law for mechanical energy at an set of elementary PD acts, thereby providing the changing of the strain from \( \varepsilon \) to \( \varepsilon + \Delta \varepsilon \).

A crystallite may emit and absorb dislocations and 0D defects under PD, thus realizing the principle of dynamic equilibrium in the form of a constant exchange of quanta \( E_{d}^{\varepsilon} (\varepsilon) \) between the field of mechanical (internal) stress and the crystallite. Between the external field of mechanical loading and the crystallite in a state of thermodynamic quasi-equilibrium are in a (rather one-way) process of exchanging PD energy. If the process of local CL restoration occurs as a result of transition from a state with energy numbers \( E_{\bar{N}_2} \) to a state with \( E_{\bar{N}_1} \) (\( \bar{N}_2 > \bar{N}_1 \)), then a quant (the sum of quanta) of quasi-elastic dislocation energy (being a quasiparticle, which we conditionally call a dislocon) is released, which can:

1) determine a new value of internal stress;
2) contribute to the growth of the temperature \( T \) of a crystallite;
3) be transferred to a neighboring crystallite upon interaction across the grain boundary (GB).

Let us obtain statistically the equilibrium scalar dislocation density \( \rho = \rho (b, d, T) \) (the sum of all dislocations, both mobile and immobile (dislocations of “forest”) having different Burgers vectors signs, \( \rho = \rho_i + \rho_r \)). To this end, we calculate the average energy \( \langle E_{d} (\varepsilon) \rangle \) of a dislocation and the number

\[\text{Assuming that in the course of an elementary PD act a dislocation may arise with its axis containing a larger quantity of atoms (segments) than the one contained at the maximal dislocation \( n > N \), the crystallite energy spectrum is augmented from above. When dislocations arise with different admissible Burgers vectors for a given CL, instead of discrete levels, the crystallite energy spectrum should consist of discrete bands, \( E_{d}^{0}, E_{d}^{1k}, \ldots, E_{d}^{nk}, \ldots, E_{d}^{n k} \), parameterized by the number 1, ..., \( n \) of atoms in the axes, and by the number \( k \) of different vectors \( b_n \), \( \forall n \).

The zones \( E_{d}^{n k}, E_{d}^{n k} \) at \( n_1 \neq n_2 \) may intersect. The dependence \( b_n = f (\varepsilon) \) then implies that \( E_{d}^{n k} = E_{d}^{n k} (\varepsilon) \).}
\[ \langle n_\varepsilon (\varepsilon) \rangle \] of atoms on its axis (see footnote 3 for partial dislocation), by the rule of averaging in ensemble, according to (10):

\[ \langle E_\varepsilon (\varepsilon) \rangle = A(\varepsilon) \sum_{n=0}^{N} E_n(\varepsilon) e^{-M(\varepsilon) E_n \varepsilon \over k_B T} = \left( Gb_\varepsilon ^3 (e^{M(\varepsilon)b_{\varepsilon}} - 1) \right)^{-1}, \quad \text{with} \quad M(\varepsilon) = \frac{4Gb_\varepsilon ^3}{k_B T}, \]

(12)

\[ \langle n_\varepsilon (\varepsilon) \rangle = A(\varepsilon) \sum_{n=0}^{N} \frac{M(\varepsilon) E_n \varepsilon}{k_B T} = e^{M(\varepsilon)b_{\varepsilon}} - 1 \equiv f_{N_\varepsilon}(b_{\varepsilon}, d, T), \]

(13)

where the factor \( \frac{1}{2} \ln \left( \frac{E_0}{\varepsilon} + Z \right) \) in \( E_n(\varepsilon) = \frac{2}{3} Gb_\varepsilon ^3 \) has been omitted, and \( \langle n_\varepsilon (\varepsilon) \rangle \) coincides with the probability distribution function for the occurrence of a dislocation with energy \( E_n(\varepsilon) \) in a grain at the equilibrium state under a PD \( \varepsilon \).

In the limit \( d = Nb \gg b \) for CG materials with a finite value \( N \sim 10^2 - 10^3 \), for SMC and NC materials, and also for grain diameters \( d \leq 5 \text{nm}, \) \( f_{N_\varepsilon}(b_{\varepsilon}, d, T) \) obeys the relation

\[ \lim_{N \to \infty} \lim_{N-M(\varepsilon) N<\infty(\varepsilon)} \left\{ f_{N_\varepsilon}(b_{\varepsilon}, d, T) = \left[ M^{-1}(\varepsilon) d/b, (e^{M(\varepsilon)b_{\varepsilon}} - 1)^{-1}, e^{-M(\varepsilon)b_{\varepsilon}} \right] \right\}, \]

(14)

The corresponding average dislocation energies for CG, SMC, and NC materials:

\[ \left\{ \lim_{N \to \infty} \lim_{N-M(\varepsilon) N<\infty(\varepsilon)} \left\{ E_\varepsilon (\varepsilon) \right\} = \frac{2d}{b} k_B T = \frac{N}{M(\varepsilon)} Gb_\varepsilon ^3, Gb_\varepsilon ^3 \right\} \]

(15)

imply that the first value is equal to the thermal energy of \( N \) atoms, being the energy of a dislocation with \( N M^{-1}(\varepsilon) \) (\( \sim 10^{-3} N \)) atoms on its axis, i.e., basically the dislocation is adjacent to the GB from inside; the second value with energy \( E_\varepsilon \) describes the fact of “germination” of a dislocation in crystallite of SMC and NC materials in the form of incomplete dislocations, as well as dislocations terminating at other dislocations, and the third value of \( M(\varepsilon)b_{\varepsilon} \) takes place, due to \( f_{N_\varepsilon} < 1 \), implying that \( \langle E_\varepsilon (\varepsilon) \rangle \rangle _{N>M(\varepsilon)b_{\varepsilon}} < \left( \frac{1}{2} Gb_\varepsilon ^3 \right) \) corresponds to the absence (on the average) in such crystallites of dislocation emergence and also of 0D defects, which leads to the softening (anti-hardening) of a sample. For NC materials, with all values \( \varepsilon, \varepsilon < \varepsilon_0 \) and a certain PD value \( \varepsilon_0, \) \( \langle E_\varepsilon (\varepsilon) \rangle \rangle _{\varepsilon<\varepsilon_0} < \left( \frac{1}{2} Gb_\varepsilon ^3 \right) \) softening may occur, whereas at \( \varepsilon \geq \varepsilon_0, \) \( \langle E_\varepsilon (\varepsilon) \rangle \rangle _{\varepsilon<\varepsilon_0} < \left( \frac{1}{2} Gb_\varepsilon ^3 \right) \) hardening may take place at a quasi-static PD. The reason for the latter is the fact that there no sufficient number of the atoms in such crystallite to produce nanopores (and thereby dislocations) within thermal-fluctuation mechanism.

The length of an average dislocation, \( \langle L_\varepsilon (\varepsilon) \rangle = b_{\varepsilon} f_{N_\varepsilon}(b_{\varepsilon}, d, T), \) and the sum of the lengths of all dislocations in an arbitrary crystallite with an accumulated PD \( \varepsilon \), according to (8),

\[ L_\varepsilon (\varepsilon) = N_0, \langle L_\varepsilon (\varepsilon) \rangle = \sqrt{2} \varepsilon m_0 \varepsilon d(1 + \varepsilon) f_{N_\varepsilon}(b_{\varepsilon}, d, T), \]

(16)

permits to determine the equilibrium scalar dislocation density \( \rho(b_{\varepsilon}, d, T) \) at the crystalline phase of a sample:

\[ \rho(b_{\varepsilon}, d, T) = B L_\varepsilon (\varepsilon) = B \frac{6\sqrt{2} \varepsilon m_0}{\pi d^2} e^{(e^{M(\varepsilon)b_{\varepsilon}} - 1)^{-1}}, \]

(17)

with allowance for a change in the grain volume (for number of materials) under PD occurring only in the direction of the loading axis, \( V(\varepsilon) = \frac{1}{6} \pi d^3(1 + \varepsilon), \) and with a constant constant \( B, \) which will be chosen from the condition that in the CG limit, \( d \gg b, \) and the absence of PD, \( \varepsilon = 0, \) we have

\[ B \left( e^{M(\varepsilon)b_{\varepsilon}} - 1 \right)^{-1} = d/b, \]

which determines the value \( B = M(0). \) In the limits of CG and NC aggregates for small PDs, the value of \( \rho(b_{\varepsilon}, d, T) \) is estimated as

\[ \left\{ \lim_{N \to \infty} \lim_{N-M(\varepsilon) N<\infty(\varepsilon)} \left\{ \rho(b_{\varepsilon}, d, T) = \frac{6\sqrt{2} \varepsilon m_0}{\pi b d} \left( (1 + \varepsilon)^{-3}, \frac{G b_\varepsilon ^3}{2 k_B T} e^{(e^{M(\varepsilon)b_{\varepsilon}} - 1)^{-1}} - m_0 \left( 10^{-10}, 10^{13} \right)^{-2}, \right\} \right\}, \]

(18)
which holds true [5] for observed dislocation densities under \( m_0 \sim 10^3 - 10^2 \) and has the form of scalar dislocation density in the H. Conrad model (see, e.g. [5]) at the CG limit. 6

Generalized flow stress law and generalized Hall–Petch law for yield strength

Following [23], suppose that the deformation (dislocation) Taylor’s hardening law [25], being valid in the region of CG materials due to the interaction energy of dislocations for tangential flow stress, \( \tau \sim \sqrt{Gb} \frac{\alpha m}{d} \), is also true for NC materials:

\[
\tau = \tau_f + \alpha Gb \sqrt{\rho},
\]

(19)
at a temperature \( T \) with a dislocation interaction constant \( \alpha \) varying for different materials within the range (0.1–0.4) for a frictional stress \( \tau_f \) at the interaction of moving dislocations with lattice defects and obstacles of non-deformation origin. Taking into account that the FS of polycrystalline sample, \( \sigma(\varepsilon) \), is proportional to \( \tau \), \( \sigma(\varepsilon) = m \tau \), \( m=3.05 \), according to (17) and (19), we obtain

\[
\sigma(\varepsilon) = \sigma_0(\varepsilon) + \alpha m Gb \frac{\sqrt{\varepsilon}}{d} \left[ \sqrt{\frac{6\sqrt{2}}{\pi}} m_0 \varepsilon Gb \frac{e^{\frac{b}{2k_B T}}}{2k_B T} (e^{\frac{b}{2k_B T}} - 1) - 1 \right]^{\frac{1}{2}}, \quad \sigma_0 = m \tau_f.
\]

Expression (20) represents the main analytical result of applying our statistical model to the determination of an equilibrium FS in the crystalline phase of a homogeneous polycrystalline aggregate in all grain ranges from CG to NC. This result is applicable to the stages of parabolic and linear hardening, up to the point of fracture and destruction. Notice the parameter values \( \sigma_0(0) = \sigma(0) = 0 \) and also \( \sigma_0(0,002) = \sigma_0 \) for \( \varepsilon = 0,002 \) in (1). The dependence \( \sigma(\varepsilon) \) determines the FS maximum \( \sigma_m(\varepsilon) = \sigma(\varepsilon)_{d=d_0} \) in dependence on the extreme grain size \( d_0 \). Based on a transcendental equation that follows from \( \partial \sigma(\varepsilon)/\partial d = 0 \),

\[
Q(\varepsilon)/d^2 \left( e^{x-1} \right)^{\frac{1}{2}} \left[ e^{x-1} - \frac{1}{2} xe^x \right] = 0, \quad x = M(\varepsilon)b/d,
\]

(21)

for a certain \( Q(\varepsilon) \) independent of \( d \), the value \( d_0 \) is determined numerically with accuracy up to 5 digits:

\[
d_0(\varepsilon,T) = \frac{b Gb^3 (1 + \varepsilon)^3}{2 \cdot 1.59363 \cdot k_B T}.
\]

(22)
The FS maximum \( \sigma_m(\varepsilon) \) of a polycrystalline aggregate without a second (soft) phase is calculated as

\[
\sigma_m(\varepsilon) = \sigma_0(\varepsilon) + \alpha m G \frac{\sqrt{\varepsilon}}{d} \left[ \frac{6\sqrt{2}}{\pi} m_0 \varepsilon Gb \frac{e^{\frac{b}{2k_B T}}}{2k_B T} (e^{\frac{b}{2k_B T}} - 1) - 1 \right]^{\frac{1}{2}}, \quad \sigma_0(\varepsilon) = K(\varepsilon)d_0^{-1/2},
\]

(23)

with a consequent restoration of the standard Hall–Petch relation (1) for any \( \varepsilon \) from the flow and parabolic hardening regions, albeit with a different coefficient \( K, k \neq K \).

For CG materials, the normal Hall–Petch law for FS at \( \varepsilon = 0,002 \) implies a relation between the Hall–Petch coefficient \( k(\varepsilon) \) and the polyhedral parameter \( m_0 \):

\[\text{---}
\]

6. The analytical representation (17) and limiting cases (18) for \( \rho(b,d,T) \) permit to qualitatively evaluate the possible dislocation substructures (DSS), which arise in the PC aggregate at accumulating of PD in view of changing curvature of the CL [11]. In particular, when the cellular or cellular-mesh DSS appear (oriented or not-oriented) the sizes of a dislocation cell is proportional to \( \Lambda \sim \sqrt{d} \), according to [Conrad H. Fenerstein S., Rice L., Mater. Sci. Eng.2, 3, 157, (1967); Bay B., Hansen N., Huges D.A., Kuhlmann-Wilsdorf D. Acta Met. Mater. 40, 2, 205 (1992)].

Taking into account, that \( \Lambda \sim 1/\sqrt{\rho} \), from (18) in CG and NC regions it follows, that for the first case the asymptotic \( \Lambda \sim \sqrt{bd}(1 + \varepsilon)^{3/2}/\varepsilon \) is true, whereas for the second case the cellular DSS disappears. With the growth of \( \varepsilon \), the size \( \Lambda \) in the CG region decreases. To be more exact, the patterns of DSS should follow from yet unknown system of equations in partial derivatives with one from them being expected of the diffusion type on the function \( \rho(b,d,T,x,y,z,t) \).
\[ \sigma(\varepsilon)|_{d>b} = \sigma_0(\varepsilon) + k(\varepsilon)d^{1/2}, \quad k(\varepsilon) = \alpha mG \frac{\sqrt{6\varepsilon}}{2m_0} \mu b M(0) M(\varepsilon) = m_0 = \frac{\pi}{6\sqrt{2}} \left(\frac{\alpha mG}{\varepsilon}\right)^2 db M(0). \quad (24) \]

To determine the values of the constant \( m_0 \) (3) let us use the known experimental values for HP coefficient \( k(0.002) \) for PC single-mode samples with BCC, FCC and HCP CL from the Table 1 with corresponding values for \( \sigma_0, G, \alpha \).

Burgers vectors with the least possible lengths \( b \), with respective most realizable sliding systems (given in the Table 2), constant of interaction for the dislocation \( \alpha \) [5, 6] and computed values of the least unit dislocations \( E_0^u \), extreme grain sizes \( d_0 \), maximal differences of \( \sigma_y \) for \( T=300K \):

**Conclusion**

A statistical approach to the derivation of generalized Hall–Petch relationships for yield strength and flow stress has been developed on a basis of analyzing the mechanical energy spectrum of each crystallite for a uniformly sized (single-modal) polycrystalline aggregate under quasi-static loading with constant strain rate \( \dot{\varepsilon} \). For a fixed value of PD \( \varepsilon \), the crystallite spectrum consisting of discrete energy levels \( E_0^u(\varepsilon) \), \( E_1^u(\varepsilon) \), \( E_2^u(\varepsilon) \), \ldots, \( E_n^u(\varepsilon) \) is considered in the equidistant approximation with a step equal to the energy of a unit dislocation and corresponding to the formation of dislocations with \( E_0^u(\varepsilon) \) for the Burgers vector of minimal length and \((n+1)\) atoms \((n\) segments) on its axis. A scenario is proposed for realizing an edge rectilinear dislocation under constant tension through the formation of a sequence of OD defects – nanopores, realizing the zones of localized plasticity (the bands of localized deformation). In a quasi-equilibrium thermodynamic state, the probabilities of finding the crystallite in a state \((m_1, m_2, ..., m_n)\) with \( m_1 \) unit dislocations (including nanopores), \( m_2 \) dislocations with 3 atoms on their axes, .... \( m_n \) dislocations with \((n+1)\) atoms on their axes, up to \( m_n \) maximal rectilinear dislocations passing through the center of the crystallographic equatorial plane, are given according to the Boltzmann distribution (9), (10) with the scale energy factor \( M(\varepsilon) \) relative to the maximal dislocation energy \( E_0^u(\varepsilon) \). The estimation of the minimal time \((7) \) for the emergence of a dislocation in a crystallite under PD allows us to estimate the number of dislocations \((8) \) with an accumulated PD \( \varepsilon \), whereas the most probable number of atoms on the dislocation axis \((13) \) obtained from the Bose–Einstein distribution leads to the analytical representation \((17) \) for equilibrium scalar dislocation density, which coincides with the experimental numerical values \((18) \) in the limits of CG (Conrad model [5]) and NC materials. An assumption of validity for the Taylor’s strain hardening mechanism \((19) \) in all grain size regions leads to the representation \((20) \) for the equilibrium flow stress \( \sigma(\varepsilon) \), starting from the first (crystalline) phase of a polycrystalline aggregate without texture. From the generalized flow stress and Hall–Petch laws for yield strength, the exact expressions are obtained for the maximal flow stress \((23) \) and extreme grain size \( d_0(\varepsilon,T) \) \((22) \), lying in the nanometer range. The value of \( d_0(\varepsilon,T) \) grows with increasing PDs and decreasing temperatures, which determine in part a temperature-dimension effect \([37]\). Note, the property: \( d_0(\varepsilon,T_1) > d_0(\varepsilon,T_2) \) for \( T_1 < T_2 \), is opposite to one marked by item 2) in the Introduction obtained within molecular dynamics simulations \([22]\). In the limit of CG aggregates, the well-known normal form of the Hall–Petch law follows from \((20) \), which makes it possible to refine the polyhedral parameter \( m_0(24) \) in connection with experiments (see Ref. [37] for further details).

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